

ABSTRACT

A technology for forming on a wafer coated with a photo resist device patterns comprised of dense patterns (41c) and isolated patterns (42c) as components. A first reticle formed with reticle patterns comprised of dense patterns (41c) of shapes corresponding to the device patterns and dense patterns formed by patterns (42a) of shapes corresponding to the isolated patterns (42c) plus a plurality of auxiliary patterns (43a) is used for exposure by $\frac{1}{2}$ of the appropriate amount of exposure as determined by the sensitivity of the resist. Next, a second reticle formed with reticle patterns comprised of dense patterns (41b) of shapes corresponding to the dense patterns (41c) of the device patterns and isolated patterns (42b) of shapes corresponding to the isolated patterns (42c) of the device patterns is used for exposure by $\frac{1}{2}$ of the appropriate amount of exposure.